L Number	Hits	Search Text	DB	Time stamp
1	4	6579374.pn. or 6630030.pn. or 6562140.pn. or 6572705.pn.	USPAT; US-PGPUB	2004/08/24 11:26
2	2	(ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) same ((control$5 or regulat$3 or optimiz$5 or monitor$3) near5 (wall or chamber or reactor) near5 temperature))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:01
3	34	(ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) and (substrate near5 temperature) and ((wall or reactor or chamber) near5 temperature))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 11:29
4	2	(ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) and ((substrate near5 temperature) with (differ$4 or increas$3 or decreas$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:06
5	12	(ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) with wall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:10
6	20	(ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) with rate with (reduc$5 or low$5 or adjust$5 or minimiz$6 or control$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 12:33
7	3122	(427/248.1,255.23,255.28,255.7).CCLS.	USPAT; US-PGPUB	2004/08/24 12:33
8	278	(427/487).CCLS.	USPAT; US-PGPUB	2004/08/24 12:33
9	5960	(118/715,719,724,725,728).CCLS.	USPAT; US-PGPUB	2004/08/24 12:34
10	1414	(117/84,85,88,105,200,201).CCLS.	USPAT; US-PGPUB	2004/08/24 12:34
11	10149	((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)	USPAT; US-PGPUB	2004/08/24 12:34
12	11	(((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) near4 wall)	USPAT; US-PGPUB	2004/08/24 13:21
13	16	(((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) near6 wall)	USPAT; US-PGPUB	2004/08/24 13:10
14	34	(((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and (ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) and ((heat$3 or temperature) near3 wall) and ((heat$3 or temperature) near3 (support or susceptor or substrate or base or wafer))	USPAT; US-PGPUB	2004/08/24 12:43

15		71	((((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and (ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) and ((deposit$3 or decompos$5 or condens$5 or contaminat$4 or coat$3) near3 (minimiz$5 or eliminat$3 or prevent$3 or avoid$5) with (chamber or vessel or reactor or wall))	USPAT; US-PGPUB	2004/08/24 13:25
16		18	((((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) same ((control$5 or regulat$3 or optimiz$5 or monitor$3) near5 (wall or chamber or reactor) near5 temperature))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:02
17		17	(((((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) same ((control$5 or regulat$3 or optimiz$5 or monitor$3) near5 (wall or chamber or reactor) near5 temperature))) not ((ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) same ((control$5 or regulat$3 or optimiz$5 or monitor$3) near5 (wall or chamber or reactor) near5 temperature)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:02
18		20	((((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) same ((control$5 or regulat$3 or optimiz$5 or monitor$3 or adjust$4) near5 (wall or chamber or reactor) near5 temperature))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:03
19		19	(((((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) same ((control$5 or regulat$3 or optimiz$5 or monitor$3 or adjust$4) near5 (wall or chamber or reactor) near5 temperature))) not ((ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) same ((control$5 or regulat$3 or optimiz$5 or monitor$3) near5 (wall or chamber or reactor) near5 temperature)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:03
20		9	((((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) and ((substrate near5 temperature) with (differ$4 or increas$3 or decreas$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:06

21	11	(((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) and (((substrate or support or pedestal or wafer) near5 temperature) with (differ$4 or increas$3 or decreas$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:36
22	10	((((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) and (((substrate or support or pedestal or wafer) near5 temperature) with (differ$4 or increas$3 or decreas$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature)))) not ((ASM.as. or Lindfors.in. or Bondestam.in.) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) and ((substrate near5 temperature) with (differ$4 or increas$3 or decreas$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:07
23	6	(((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) with (wall or reactor or chamber) with (reduc$5 or minimiz$6 or lower or low$3 or prevent$5 or eliminat$6) with rate)	USPAT; US-PGPUB	2004/08/24 13:17
24	57	(((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) with (wall or reactor or chamber) with (reduc$5 or minimiz$6 or lower or low$3 or prevent$5 or eliminat$6))	USPAT; US-PGPUB	2004/08/24 13:13
25	51	((((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) with (wall or reactor or chamber) with (reduc$5 or minimiz$6 or lower or low$3 or prevent$5 or eliminat$6))) not ((((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) with (wall or reactor or chamber) with (reduc$5 or minimiz$6 or lower or low$3 or prevent$5 or eliminat$6) with rate))	USPAT; US-PGPUB	2004/08/24 13:13

26	11	(((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) with (wall or reactor or chamber) with (rate near4 (ALE or ALD or deposit$3 or grow$4)))	USPAT; US-PGPUB	2004/08/24 13:18
27	37	((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) near4 wall)	USPAT; US-PGPUB	2004/08/24 13:21
28	26	(((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) near4 wall)) not (((((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and ((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) near4 wall))	USPAT; US-PGPUB	2004/08/24 13:21
29	36	((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) same ((deposit$3 or decompos$5 or condens$5 or contaminat$4 or coat$3 or grow$4) near3 (minimiz$5 or eliminat$3 or prevent$3 or avoid$5 or reduc$6 or low$4) with (chamber or vessel or reactor or wall) with (hot or cold or temperature or heat$3 or cool$3)))	USPAT; US-PGPUB	2004/08/24 13:24
30	27	(((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) same ((deposit$3 or decompos$5 or condens$5 or contaminat$4 or coat$3 or grow$4) near3 (minimiz$5 or eliminat$3 or prevent$3 or avoid$5 or reduc$6 or low$4) with (chamber or vessel or reactor or wall) with (hot or cold or temperature or heat$3 or cool$3)))) not (((((427/248.1,255.23,255.28,255.7).CCLS.) ((427/487).CCLS.) ((118/715,719,724,725,728).CCLS.) ((117/84,85,88,105,200,201).CCLS.)) and (ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) and ((deposit$3 or decompos$5 or condens$5 or contaminat$4 or coat$3) near3 (minimiz$5 or eliminat$3 or prevent$3 or avoid$5) with (chamber or vessel or reactor or wall)))	USPAT; US-PGPUB	2004/08/24 13:25
31	25	((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) same ((deposit$3 or decompos$5 or condens$5 or contaminat$4 or coat$3 or grow$4) with (wall) with (hot or cold or temperature or heat$3 or cool$3)))	USPAT; US-PGPUB	2004/08/24 13:28
32	10	(((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) same ((deposit$3 or decompos$5 or condens$5 or contaminat$4 or coat$3 or grow$4) with (wall) with (hot or cold or temperature or heat$3 or cool$3)))) not (((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) same ((deposit$3 or decompos$5 or condens$5 or contaminat$4 or coat$3 or grow$4) near3 (minimiz$5 or eliminat$3 or prevent$3 or avoid$5 or reduc$6 or low$4) with (chamber or vessel or reactor or wall) with (hot or cold or temperature or heat$3 or cool$3))))	USPAT; US-PGPUB	2004/08/24 13:28
33	11	((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) and ((wall with (substrate or support or base or susceptor or wafer) with (higher or lower or different or difference or greater or lesser or increas$4 or decreas$4) with (temperature))))	USPAT; US-PGPUB	2004/08/24 13:31

34	0	((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) and ((wall with (substrate or support or base or susceptor or wafer) with (higher or lower or different or difference) with (temperature))))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:32
35	14	((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) with ((minimiz$5 or eliminat$3 or prevent$3 or avoid$5) with (chamber or vessel or reactor or wall)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:33
36	2	((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) with ((minimiz$5 or eliminat$3 or prevent$3 or avoid$5) with (chamber or vessel or reactor or wall) with (hot or cold or temperature or heat$3 or cool$3)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:34
37	1	((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) same ((deposit$3 or decompos$5 or condens$5 or contaminat$4 or coat$3) with (wall) with (hot or cold or temperature or heat$3 or cool$3)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:35
38	6	((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$6))) near4 wall)	EPO; JPO; IBM_TDB	2004/08/24 13:35
39	0	((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) and (((substrate or support or pedestal or wafer) near5 temperature) with (differ$4 or increas$3 or decreas$3 or higher or lower or greater or lesser) with ((wall or reactor or chamber) near5 temperature)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:37
40	12	((ALE or ALD or (atomic adj layer adj (deposit$3 or epitax$5))) and (((substrate or support or pedestal or wafer) near5 temperature) with ((wall or reactor or chamber) near5 temperature)))	EPO; JPO; DERWENT; IBM_TDB	2004/08/24 13:37